

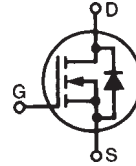
HiPerFET™ Power MOSFETs

N-Channel Enhancement Mode
High dv/dt, Low t_{rr} , HDMOS™ Family

IXFH/IXFM 10 N100
IXFH/IXFM 12 N100

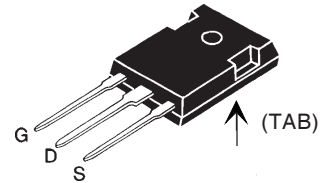
V_{DSS}	I_{D25}	$R_{DS(on)}$
1000 V	10 A	1.20 Ω
1000 V	12 A	1.05 Ω

$t_{rr} \leq 250$ ns

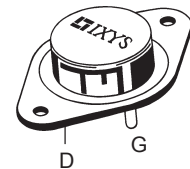


Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	1000	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C ; $R_{GS} = 1$ M Ω	1000	V
V_{GS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	10N100 12N100	10 12 A
I_{DM}	$T_C = 25^\circ\text{C}$, pulse width limited by T_{JM}	10N100 12N100	40 48 A
I_{AR}	$T_C = 25^\circ\text{C}$	10N100 12N100	10 12 A
E_{AR}	$T_C = 25^\circ\text{C}$	30	mJ
dv/dt	$I_S \leq I_{DM}$, di/dt ≤ 100 A/ μs , $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$, $R_G = 2$ Ω	5	V/ns
P_D	$T_C = 25^\circ\text{C}$	300	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
T_L	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-204 = 18 g, TO-247 = 6 g	

TO-247 AD (IXFH)



TO-204 AA (IXFM)



G = Gate, D = Drain,
S = Source, TAB = Drain

Features

- International standard packages
- Low $R_{DS(on)}$ HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
- easy to drive and to protect
- Fast intrinsic Rectifier

Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_{DSS}	$V_{GS} = 0$ V, $I_D = 3$ mA	1000		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 4$ mA	2.0		4.5 V
I_{GSS}	$V_{GS} = \pm 20$ V _{DC} , $V_{DS} = 0$			± 100 nA
I_{DSS}	$V_{DS} = 0.8 \cdot V_{DSS}$, $T_J = 25^\circ\text{C}$ $V_{GS} = 0$ V, $T_J = 125^\circ\text{C}$			250 μA 1 mA
$R_{DS(on)}$	$V_{GS} = 10$ V, $I_D = 0.5 \cdot I_{D25}$ Pulse test, $t \leq 300$ μs , duty cycle $d \leq 2$ %	10N100 12N100		1.20 Ω 1.05 Ω

Fig. 1 Output Characteristics

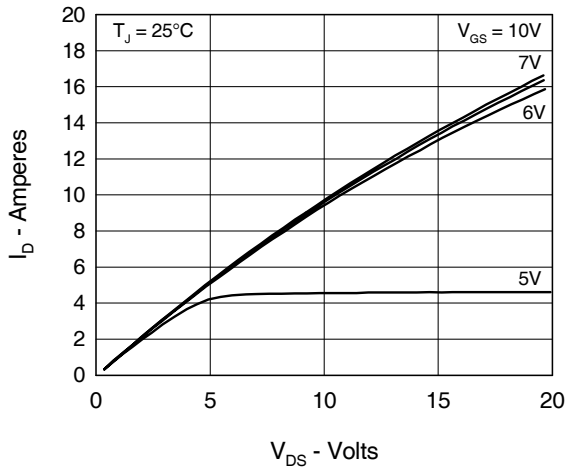


Fig. 2 Input Admittance

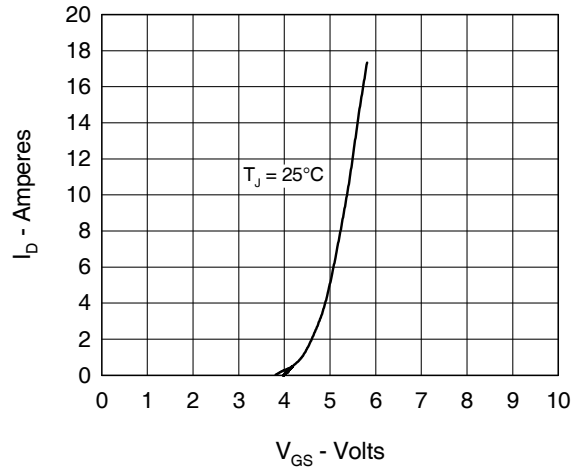


Fig. 3 $R_{DS(on)}$ vs. Drain Current

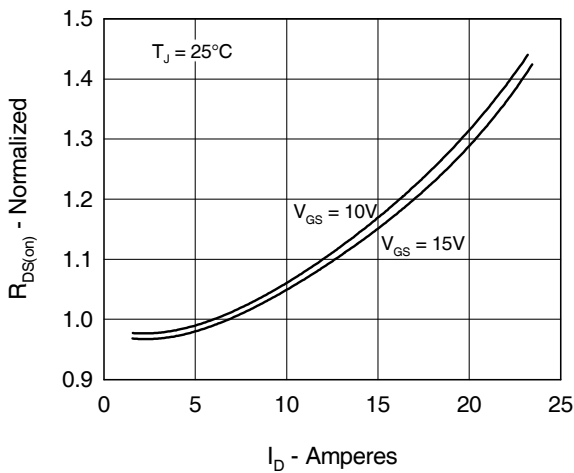


Fig. 4 Temperature Dependence of Drain to Source Resistance

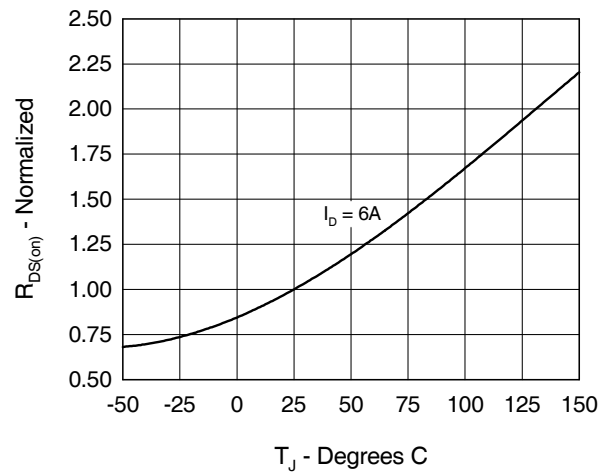


Fig. 5 Drain Current vs. Case Temperature

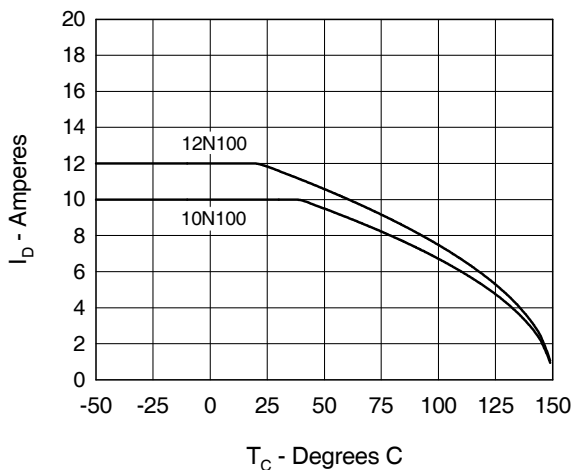


Fig. 6 Temperature Dependence of Breakdown and Threshold Voltage

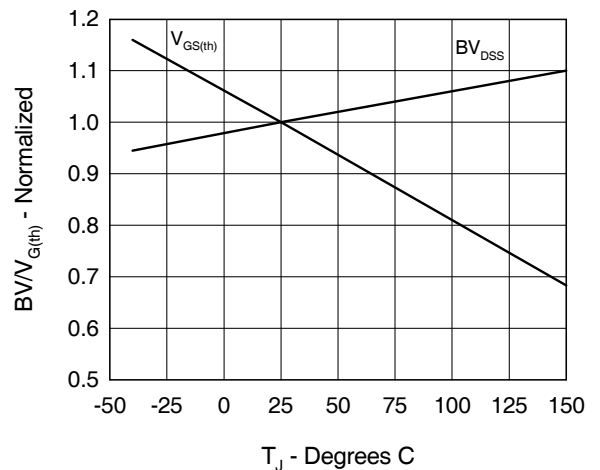


Fig.7 Gate Charge Characteristic Curve

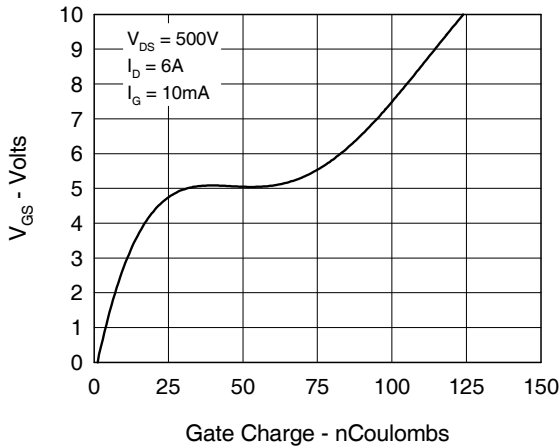


Fig.8 Capacitance Curves

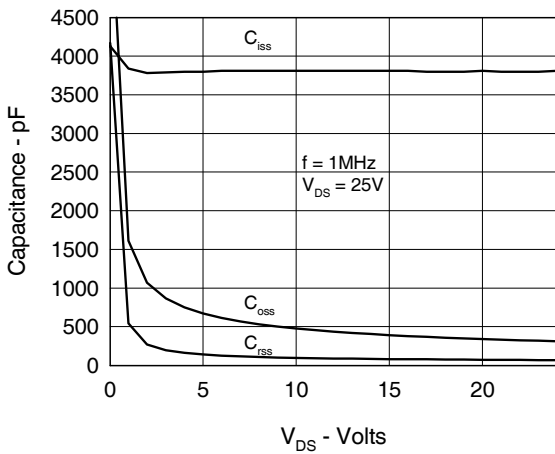


Fig.9 Source Current vs. Source to Drain Voltage

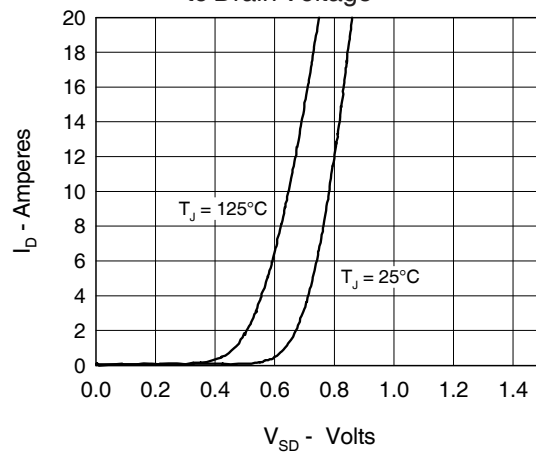
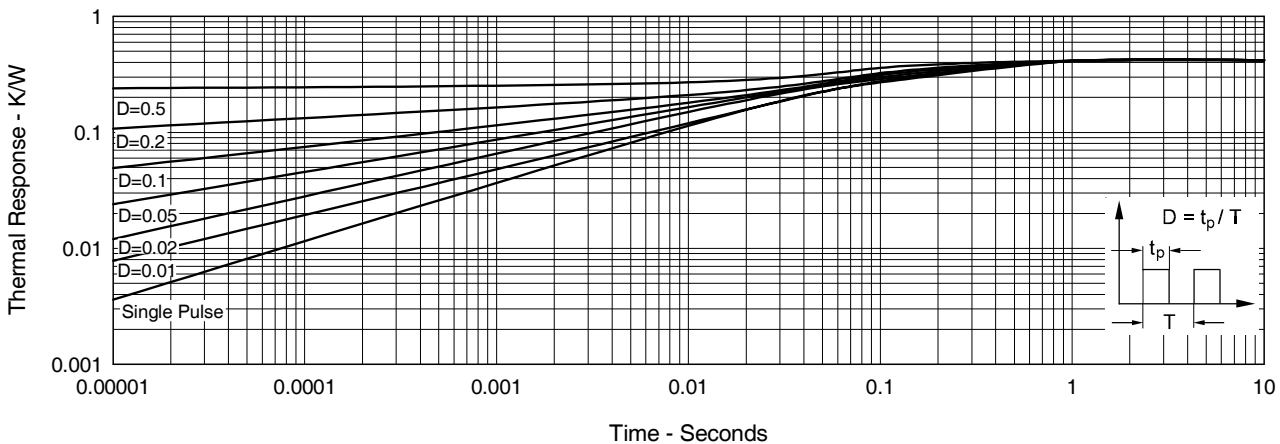


Fig.10 Transient Thermal Impedance



IXYS reserves the right to change limits, test conditions, and dimensions.